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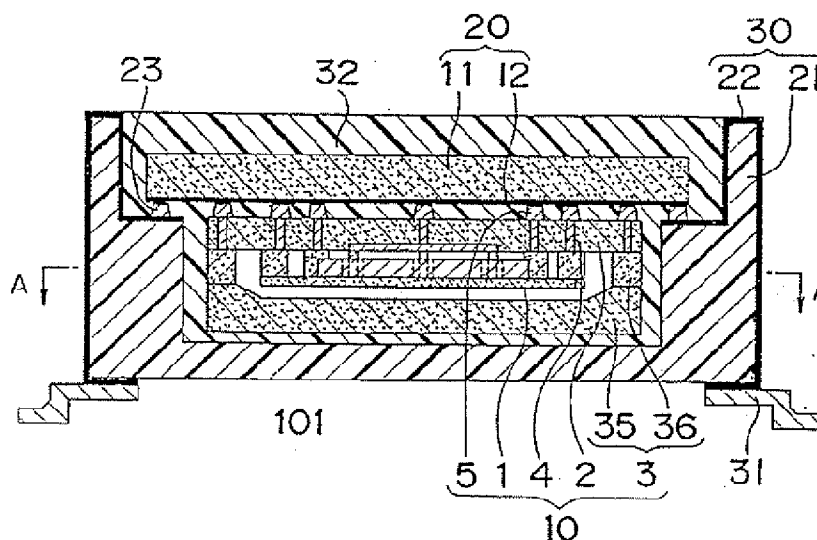
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(54) Title: SENSOR DEVICE, SENSOR SYSTEM AND METHODS FOR MANUFACTURING THEM



(57) Abstract: A sensor system includes a sensor device (10) and an integrated circuit (20) for driving the device (10). The device (10) includes a sensor body (1) of a silicon-based material, an upper sealing member (2) of a silicon-based material, and a lower sealing member (3) of a silicon-based material. The upper sealing member (2) and the lower sealing member (3) are joined together to cooperatively house the body (1) therewithin in an airtight manner. The device (10) and the circuit (20) are formed as a stacked body. The body (1) is electrically connected to a wiring pattern (12) of the circuit (20) through a conductive through-path (4) penetrating the upper sealing member (4) and a mounting electrode (5) provided on an outer surface of the upper sealing member (2). The device (10) is connected to an MID substrate (30) through the circuit (20).



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